

BC808-25LT1G, BC808-40LT1G

General Purpose Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-25	V
Collector – Base Voltage	V_{CBO}	-30	V
Emitter – Base Voltage	V_{EBO}	-5.0	V
Collector Current – Continuous	I_C	-500	mA _{dc}

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

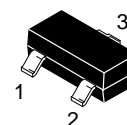
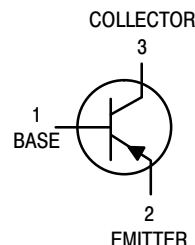
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



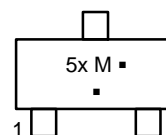
ON Semiconductor®

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SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



- 5x = Device Code
x = F or G
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC808–25LT1G, BC808–40LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = –10 mA)	V _{(BR)CEO}	–25	–	–	V
Collector–Emitter Breakdown Voltage (V _{EB} = 0, I _C = –10 μA)	V _{(BR)CES}	–30	–	–	V
Emitter–Base Breakdown Voltage (I _E = –1.0 μA)	V _{(BR)EBO}	–5.0	–	–	V
Collector Cutoff Current (V _{CB} = –20 V) (V _{CB} = –20 V, T _J = 150°C)	I _{CBO}	–	–	–100 –5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain (I _C = –100 mA, V _{CE} = –1.0 V) (I _C = –500 mA, V _{CE} = –1.0 V)	h _{FE} BC808–25LT1G BC808–40LT1G	160 250 40	– – –	400 600 –	–
Collector–Emitter Saturation Voltage (I _C = –500 mA, I _B = –50 mA)	V _{CE(sat)}	–	–	–0.7	V
Base–Emitter On Voltage (I _C = –500 mA, I _B = –1.0 V)	V _{BE(on)}	–	–	–1.2	V
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 Vdc, f = 100 MHz)	f _T	100	–	–	MHz
Output Capacitance (V _{CB} = –10 V, f = 1.0 MHz)	C _{obo}	–	10	–	pF

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping†
BC808–25LT1G	5F	SOT–23 (Pb–Free)	3000 / Tape & Reel
SBC808–25LT1G			
BC808–40LT1G	5G	SOT–23 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC808-25LT1G, BC808-40LT1G

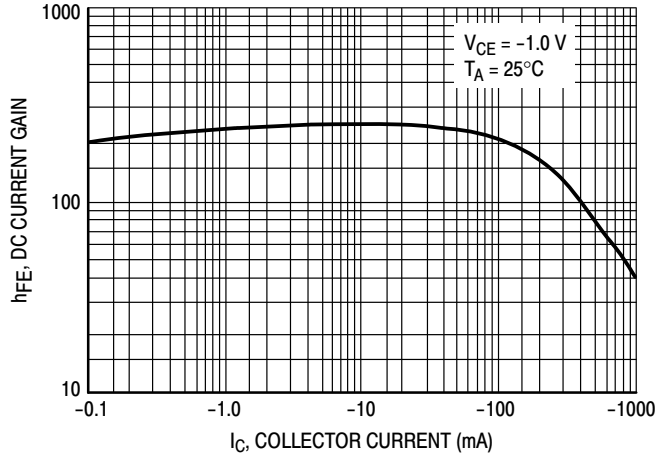


Figure 1. DC Current Gain

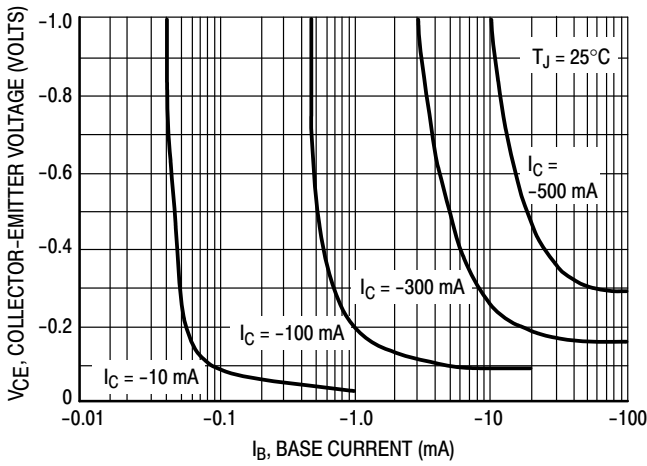


Figure 2. Saturation Region

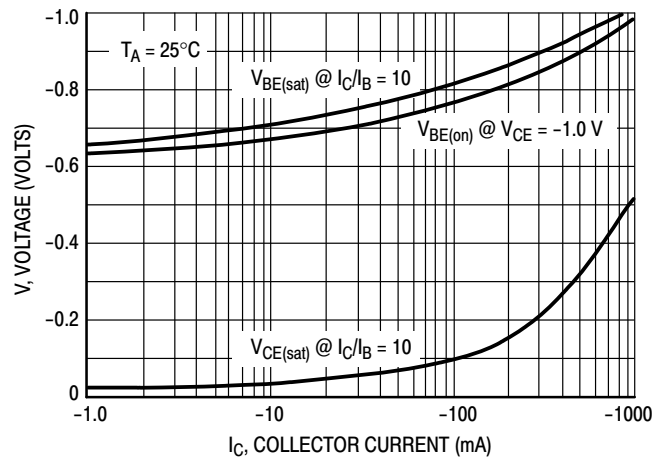


Figure 3. "On" Voltages

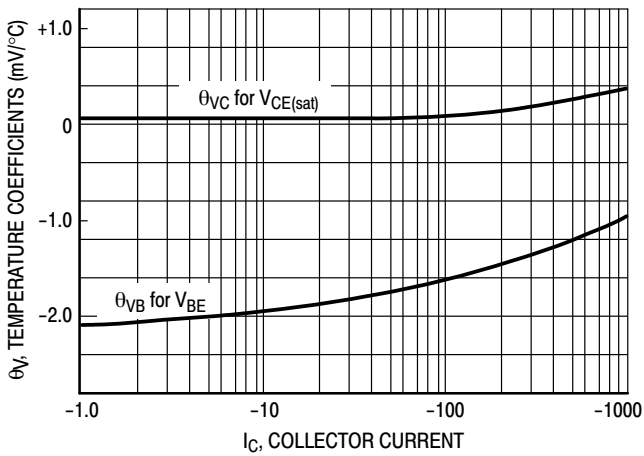


Figure 4. Temperature Coefficients

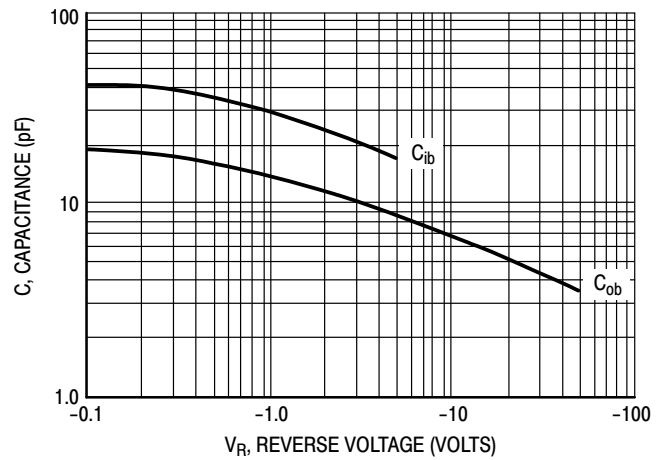
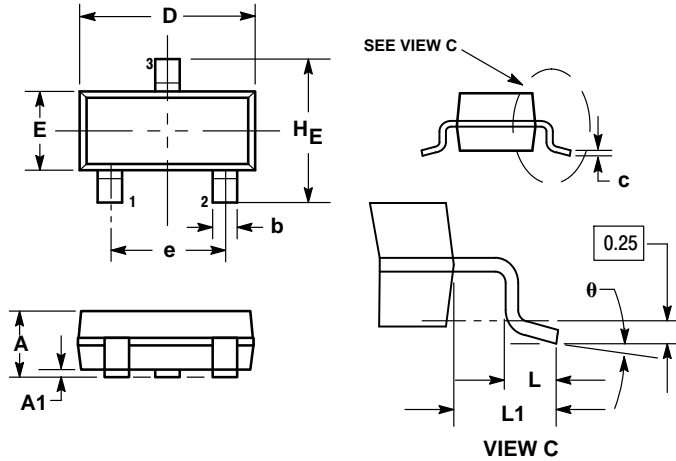


Figure 5. Capacitances

BC808-25LT1G, BC808-40LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP

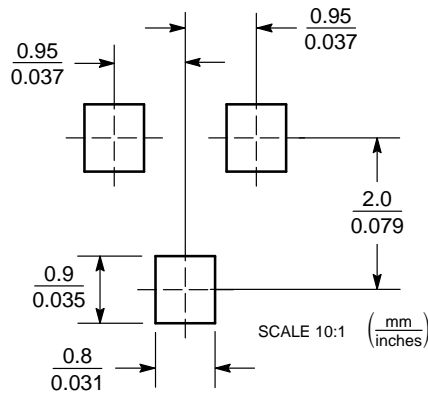


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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